L Number		Search Text	DB	Time stamp
-	2993		USPAT;	2002/10/16 09:02
			US-PGPUB;	
			EPO; JPO;	
	200-	(San)	DERWENT	2002/10/15 22 22
-	2825	(fowler near5 Nordheim near5 tunnel\$4) and	USPAT;	2002/10/16 09:03
		memory	US-PGPUB; EPO; JPO;	
			DERWENT	
_	1697	((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:16
	200,	and memory) and (insulation insulating	US-PGPUB;	
1		insulator)	EPO; JPO;	
			DERWENT	
-	1500	(((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:04
		and memory) and (insulation insulating	US-PGPUB;	
!		insulator)) and transistor	EPO; JPO;	
			DERWENT	0000/10/15 00 1:
-	718	((((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:14
		and memory) and (insulation insulating insulator)) and transistor) and MOS	US-PGPUB; EPO; JPO;	
		insuratory, and transistory and MOS	DERWENT	
_	823	(fowler near5 Nordheim near5 tunnel\$4) and	USPAT;	2002/10/16 09:15
	023	(MOS near5 transistor)	US-PGPUB;	2002, 10, 10 05.15
		,	EPO; JPO;	
			DERWENT	
-	537	((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:17
	,	and (MOS near5 transistor)) and	US-PGPUB;	
		(insulation insulating insulator)	EPO; JPO;	
	400		DERWENT	0000/10/15 00 15
-	498	(((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:18
	!	and (MOS near5 transistor)) and (insulation insulating insulator)) and	US-PGPUB; EPO; JPO;	
	!	(floating near5 gate)	DERWENT	
_	475	((((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 09:52
	1,3	and (MOS near5 transistor)) and	US-PGPUB;	,,
	· '	(insulation insulating insulator)) and	EPO; JPO;	
		(floating near5 gate)) and (control near5	DERWENT	
	,	gate)		
-	104	((((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 11:07
		and (MOS near5 transistor)) and	US-PGPUB;	
		(insulation insulating insulator)) and	EPO; JPO; DERWENT	
		<pre>(floating near5 gate)) and (control near5 gate)) and (poly near5 (gate block))</pre>	DELMENT	
_	943	(fowler near5 Nordheim near5 tunnel\$4) and	USPAT;	2002/10/16 11:08
	3.3	(((metal adj oxide adj semiconductor) MOS)	US-PGPUB;	
		near5 transistor)	EPO; JPO;	
			DERWENT	
-	778	((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 11:10
]		and (((metal adj oxide adj semiconductor)	US-PGPUB;	ļ
1 1		MOS) near5 transistor)) and (control adj	EPO; JPO;	
	F 0.4	gate) and (floating adj gate)	DERWENT	2002/10/16 11:14
-	524	<pre>(((fowler near5 Nordheim near5 tunnel\$4) and (((metal adj oxide adj semiconductor)</pre>	USPAT; US-PGPUB;	2002/10/10 11:14
		MOS) near5 transistor)) and (control adj	EPO; JPO;	
		gate) and (floating adj gate)) and	DERWENT	
,		(insulator insulation insulating)		
-	348	((((fowler near5 Nordheim near5 tunnel\$4)	USPAT;	2002/10/16 11:15
		and (((metal adj oxide adj semiconductor)	US-PGPUB;	
	,	MOS) near5 transistor)) and (control adj	EPO; JPO;	
		gate) and (floating adj gate)) and	DERWENT	,
		(insulator insulation insulating)) and		
L		((poly polysilicon) near5 gate)	L	L